



# Solid State Devices, Inc.

14701 Firestone Blvd \* La Mirada, Ca 90638  
Phone: (562) 404-7855 \* Fax: (562) 404-1773  
ssdi@ssdi-power.com \* www.ssdi-power.com

**SDR998CT/3  
thru  
SDR9912CT/3**

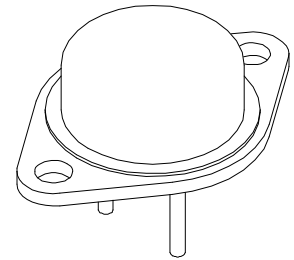
## DESIGNER'S DATA SHEET

### Features:

- UltraFast Recovery 60 nsec typical
- High Surge Rating
- Low Reverse Leakage Current
- Low Forward Voltage Drop
- Low Junction Capacitance
- Hermetically Sealed Package
- Gold Eutectic Die Attach available
- Ultrasonic Aluminum Wire Bonds
- TX, TXV, Face Level Screening Available Consult Factory.

**100 AMP  
800 -1200 Volts  
80 nsec  
ULTRA FAST COMMON CATHODE  
CENTERTAP RECTIFIER**

**TO-3**



Maximum Ratings		Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking Voltage	SDR998CT/3	$V_{RRM}$	800	Volts
	SDR999CT/3		900	
	SDR9910CT/3	$V_{RWM}$	1000	
	SDR9911CT/3		1100	
	SDR9912CT/3	$V_R$	1200	
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, $T_A = 25^\circ\text{C}$ ) note 1		$I_o$	100	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, $T_A = 25^\circ\text{C}$ , per leg)		$I_{FSM}$	600	Amps
Operating & Storage Temperature		Top & Tstg	-65 to +200	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case, each individual diode Junction to Case, note 1		$R_{qJE}$	1.1 0.75	$^\circ\text{C/W}$

Note 1: Both legs in parallel

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RU0115B

DOC



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Electrical Characteristics		Symbol	Min	Max	Units
<b>Instantaneous Forward Voltage Drop</b> ( $T_A = 25^\circ\text{C}$ , 300 $\mu\text{sec}$ pulse)	$I_F = 25\text{A dc}$ $I_F = 50\text{A dc}$	$V_{F1}$	—	1.85 2.1	Volts
<b>Instantaneous Forward Voltage Drop</b> ( $T_A = -55^\circ\text{C}$ , 300 $\mu\text{sec}$ pulse) ( $T_A = 100^\circ\text{C}$ , 300 $\mu\text{sec}$ pulse)	$I_F = 25\text{A dc}$ $I_F = 25\text{A dc}$	$V_{F2}$	—	1.75 1.9	Volts
<b>Reverse Leakage Current</b> (Rated $V_R$ , $T_A = 25^\circ\text{C}$ , 300 $\mu\text{sec}$ pulse minimum)		$I_{R1}$	—	100	mA
<b>Reverse Leakage Current</b> (Rated $V_R$ , $T_A = 100^\circ\text{C}$ , 300 $\mu\text{sec}$ pulse minimum)		$I_{R2}$	—	10	mA
<b>Junction Capacitance</b> ( $V_R = 10\text{ Vdc}$ , $T_A = 25^\circ\text{C}$ , $f = 1\text{MHz}$ )		$C_J$	—	100	pF
<b>Reverse Recovery Time</b> ( $I_F = 500\text{ mA}$ , $I_R = 1\text{A}$ , $I_{RR} = 0.25\text{A}$ )	$T_A = 25^\circ\text{C}$	$t_{rr}$	—	80	nsec

